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Claims

1. A method for error correction decoding ECC encoded data stored in a solid-state storage device having a plurality of storage cells, comprising the steps of:

obtaining parametric values from a set of the storage cells;

generating a block of stored ECC encoded data, using the obtained parametric values;

forming erasure information for the block of stored ECC encoded data, using the obtained parametric values; and

error correction decoding the block of stored ECC encoded data with reference to the erasure information.

- 20 2. The method of claim 1, comprising reading the set of storage cells.
- 3. The method of claim 1, comprising generating logical values with respect to the obtained parametric values.
 - 4. The method of claim 1, comprising comparing the obtained parametric values against a range.
- 30 5. The method of claim 1, wherein the device is a magnetoresistive solid-state storage device.

6. The method of claim 5, wherein the obtained parametric values include a resistance value or a time value for each of the set of storage cells, the obtained parametric values being derived from a sense current.

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7. The method of claim 1, wherein the forming step comprises comparing the obtained parametric values against a range to infer physical failures amongst the storage cells.

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- 8. The method of claim 1, wherein the generating step comprises generating logical values for a plurality of symbols of the block of encoded data, and the forming step comprises identifying one or more of the symbols as an erasure.
- 9. The method of claim 8, wherein the erasure information identifies one or more symbols in the block of encoded data where a logical value could not be obtained from the parametric values.
- 10. The method of claim 8, wherein the erasure information identifies one or more symbols in the block of encoded data where a logical value obtained from the parametric values is considered to be unreliable.
- 11. The method of claim 1, wherein the decoding step comprises identifying the location of zero or more errors in the block of encoded data, with reference to the erasure information; and replacing each identified error with a calculated correct value.

- 12. The method of claim 8, wherein the decoding step comprises identifying the location of zero or more failed symbols in the block of encoded data, using the erasure information; and replacing each identified failed symbol with a calculated correct value.
- 13. The method of claim 1, comprising the step of writing back corrected encoded data to the storage cells.
- 10 14. The method of claim 13, wherein the write-back step comprises selectively writing back corrected encoded data to the storage cells, with reference to the erasure information.
- 15. The method of claim 14, wherein the write-back step comprises selectively not writing back corrected encoded data to storage cells which are determined as affected by physical failures.
- 20 16. The method of claim 1, further comprising the steps of:

encoding a logical unit of original information to form a block of ECC encoded data; and

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storing the block of ECC encoded data in the array of storage cells;

wherein the decoding step attempts to recover the logical unit of original information from the stored block of ECC encoded data.

17. A solid state storage device, comprising:

at least one array of storage cells; and

an array controller for obtaining parametric values from a set of the storage cells and generating a block of stored ECC encoded data using the obtained parametric values, including forming erasure information for the block of stored ECC encoded data using the obtained parametric values; and

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an ECC decoding unit for decoding the block of stored ECC encoded data with reference to the erasure information.

- 15 18. The device of claim 1, wherein the device is a magnetoresistive solid-state storage device.
 - 19. A magnetoresistive solid-state storage device, comprising:

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at least one array of magnetoresistive storage cells;

an ECC coding unit for receiving original information and forming a block of ECC encoded data;

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a controller for storing the block of ECC encoded data in the array of storage cells;

an array controller for obtaining parametric values
from a set of the storage cells and generating a block of
stored ECC encoded data using the obtained parametric
values, including forming erasure information for the

block of stored ECC encoded data using the obtained parametric values; and

- an ECC decoding unit for decoding the block of stored 5 ECC encoded data with reference to the erasure information.
 - 20. An apparatus incorporating a magnetoresistive storage device according to claim 19.